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ERRATA

Erratum: Auger recombination in low-band-gap *n*-type InGaAs [Appl. Phys. Lett. 79, 3272 (2001)]

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In the original article, on the last page, we state that "To compare our results to the literature, we used the expression $\tau=1/Cn^2$, and found the Auger coefficient for passivated 0.74, 0.60, and 0.50 eV n-InGaAs to be 1.8, 1.2, and 0.7 $\times 10^{-28}$ cm⁶/s, respectively." The order was reversed, and the sentence should read "To compare our results to the literature, we used the expression, $\tau=1/Cn^2$, and found the Auger coefficient for passivated 0.74, 0.60, and 0.50 eV n-InGaAs to be 0.7, 1.2, and 1.8×10^{-28} cm⁶/s, respectively."